

# Addressing DDR5 design challenges with IBIS-AMI modeling techniques

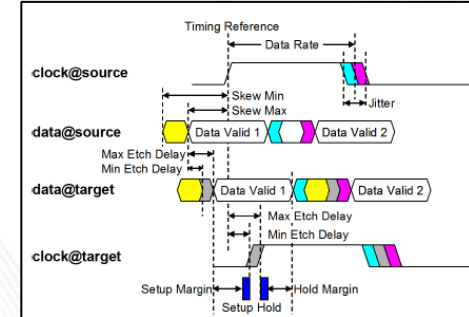
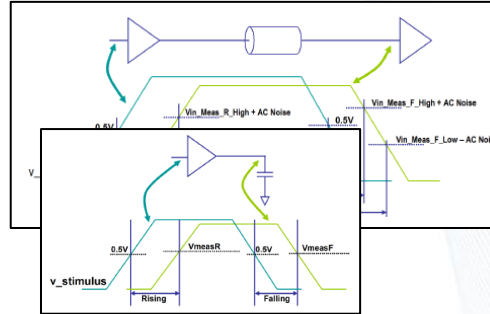
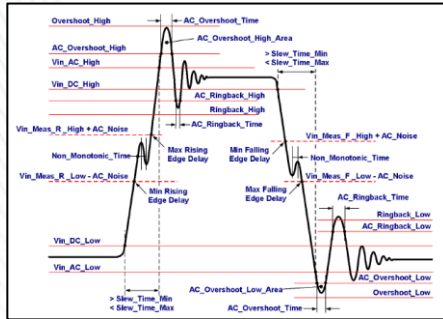
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# Agenda

- Traditional DDR analysis
- Eyes and probabilities
- IBIS-AMI models
- DDR5 topologies and transactions
- Optimizing terminations
- Pulse response analysis
- Applying equalization
- Summary

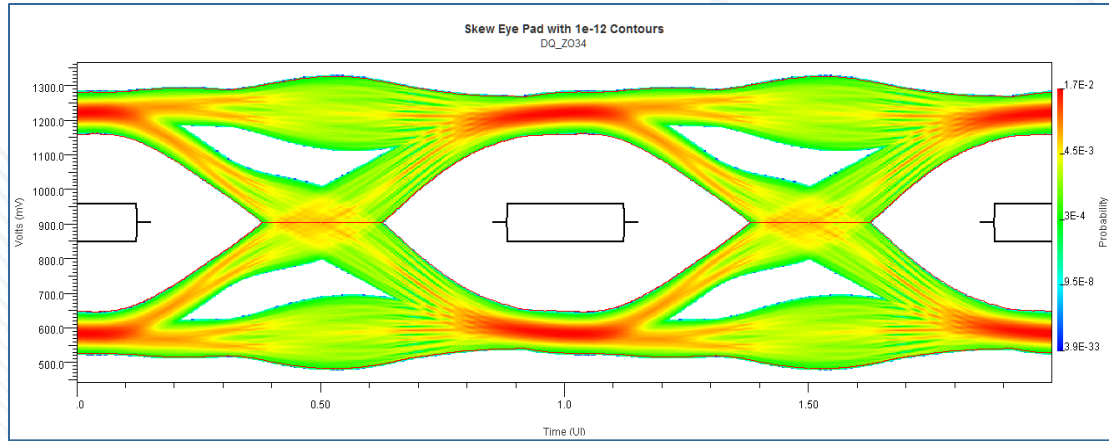
# Traditional DDR Analysis



## Signal Integrity + Flight Time Extraction + Timing Analysis

- Combined signal integrity + timing analysis  
➔ voltage and timing margins
- SI analysis < 100 data bits
- Margins computed based on worst case data

# Eyes and Probabilities



- SerDes analysis techniques used to predict eye characteristics > 1M bits
- Eye margins measured against reference mask
  - Timing / skew adjustments are assumed

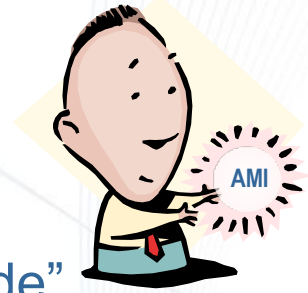
# IBIS-AMI Models

## Goals

- **Interoperable:** different vendor models work together
- **Portable:** one model runs in multiple simulators
- **Flexible:** supports Statistical and Time-Domain simulation
- **High Performance:** simulates a million bits per CPU minute
- **Accurate:** high correlation to simulations / measurement

## Assumptions

- “High impedance node” between analog I/O & equalization circuitry
- Analog I/O operates in linear region
- EQ behavior modeled by code linked into simulator
- EQ models meet AMI API



# Serial Channels vs. DDR Topologies

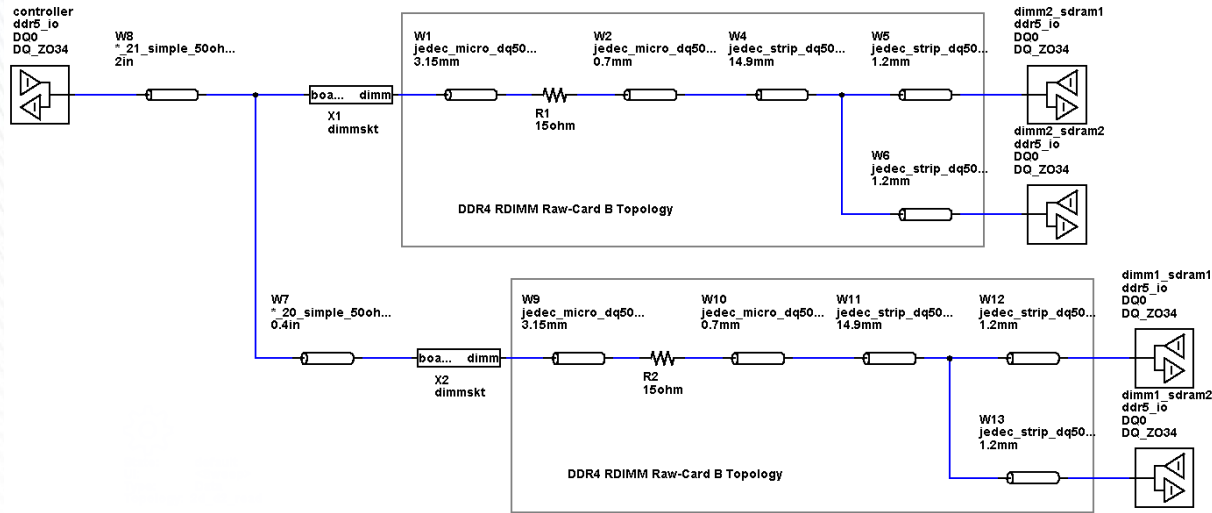
## Serial Channels

- Differential
- Long and lossy
- Unidirectional
- Continuous operation
- Simple impedance control
- Point to point topology

## DDR Topologies

- Single-ended & differential
- Short and reflective
- Bidirectional
- Communicate in bursts
- Complex impedance control
- Multiple sources / loads with long branches

# DDR5 Topologies and Transactions



1. (Write) Controller to DIMM1
2. (Write) Controller to DIMM2
3. (Read) DIMM1 to Controller
4. (Read) DIMM2 to Controller

# Optimizing Terminations

## Driver settings:

- DQ\_ZO34            Generic DDR5 34 Ohm Driver
- DQ\_ZO40            Generic DDR5 40 Ohm Driver
- DQ\_ZO48            Generic DDR5 48 Ohm Driver

## Receiver / terminator settings:

- DQ\_IN\_ODTOFF      Generic DDR5 Receiver with No ODT
- DQ\_IN\_ODT34        Generic DDR5 Receiver with 34 ohm ODT
- DQ\_IN\_ODT40        Generic DDR5 Receiver with 40 ohm ODT
- DQ\_IN\_ODT48        Generic DDR5 Receiver with 48 ohm ODT
- DQ\_IN\_ODT60        Generic DDR5 Receiver with 60 ohm ODT
- DQ\_IN\_ODT80        Generic DDR5 Receiver with 80 ohm ODT
- DQ\_IN\_ODT120       Generic DDR5 Receiver with 120 ohm ODT
- DQ\_IN\_ODT240       Generic DDR5 Receiver with 240 ohm ODT

Each transaction:

(Driver) \* (Receiver) \* (Terminator)\* (Terminator) \* (Terminator)

= 3 \* 8 \* 8 \* 8 \* 8

= 12,288 combinations per transaction

\* 4 transactions

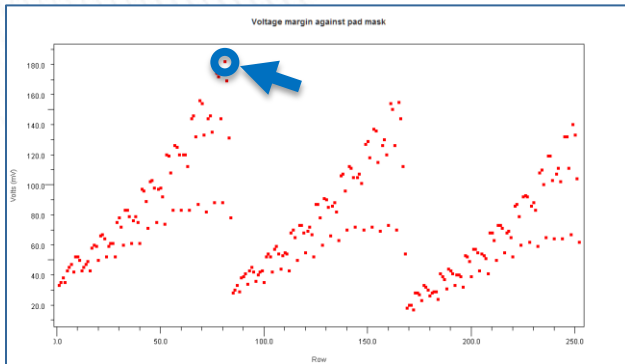
= 49,152 total termination settings (!)



# Finding The Best Case

Variable:	Type:	Format:	Variation Group:	Value 1:	Value 2:	Value 3:	Value 4:	Value 5:	Value 6:	Value 7:
\$controller:t1:model	IBIS Model	List	<none>	DQ_Z034	DQ_Z040	DQ_Z048				
\$dimm1_sdram:t1:model	IBIS Model	List	<none>	DQ_IN_ODT34	DQ_IN_ODT40	DQ_IN_ODT48	DQ_IN_ODT60	DQ_IN_ODT80	DQ_IN_ODT120	DQ_IN_ODT240
\$dimm1_sdram2:t1:model	IBIS Model	List	<none>	DQ_IN_ODT120	DQ_IN_ODT240	DQ_IN_ODTOFF				
\$dimm2_sdram:t1:model	IBIS Model	List	dim2	DQ_IN_ODT60	DQ_IN_ODT80	DQ_IN_ODT120	DQ_IN_ODT240			
\$dimm2_sdram2:t1:model	IBIS Model	List	dim2	DQ_IN_ODT60	DQ_IN_ODT80	DQ_IN_ODT120	DQ_IN_ODT240			
\$UI	UI	List	<none>	0.313ns - ddr5_dq_3200						

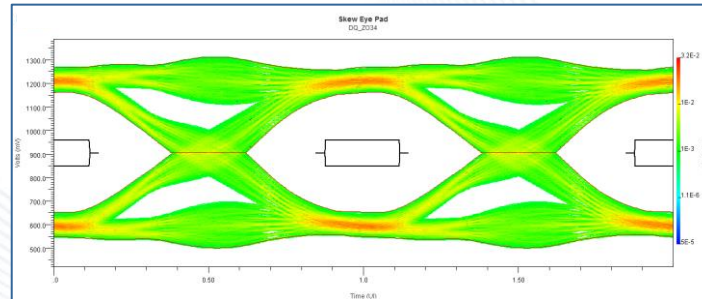
252 cases tested (out of a possible 12,288)



Voltage margin distribution

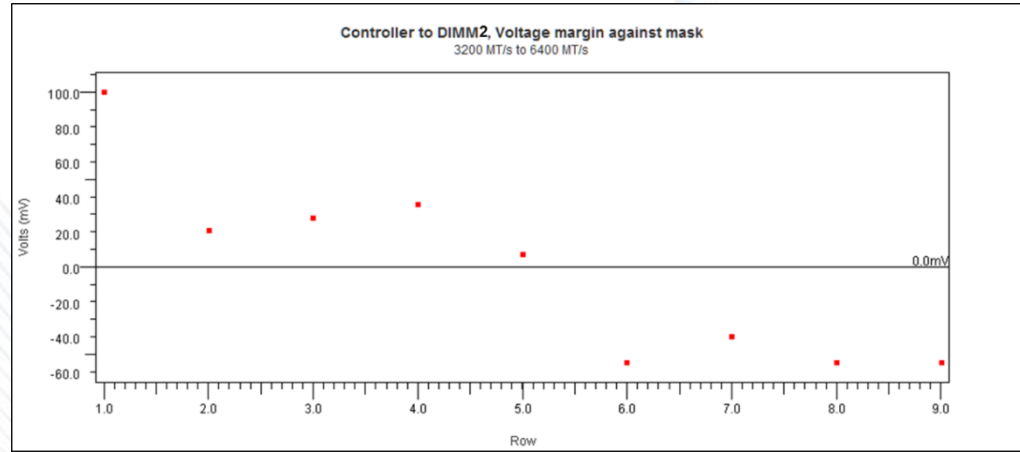
\$CONTROLLER:T1:MODEL	DQ_Z034
\$DIMM1_SDRAM1:T1:MODEL	DQ_IN_ODT240
\$DIMM1_SDRAM2:T1:MODEL	DQ_IN_ODTOFF
\$DIMM2_SDRAM1:T1:MODEL	DQ_IN_ODT60
\$DIMM2_SDRAM2:T1:MODEL	DQ_IN_ODT60

Best case conditions



Voltage and timing margin against mask

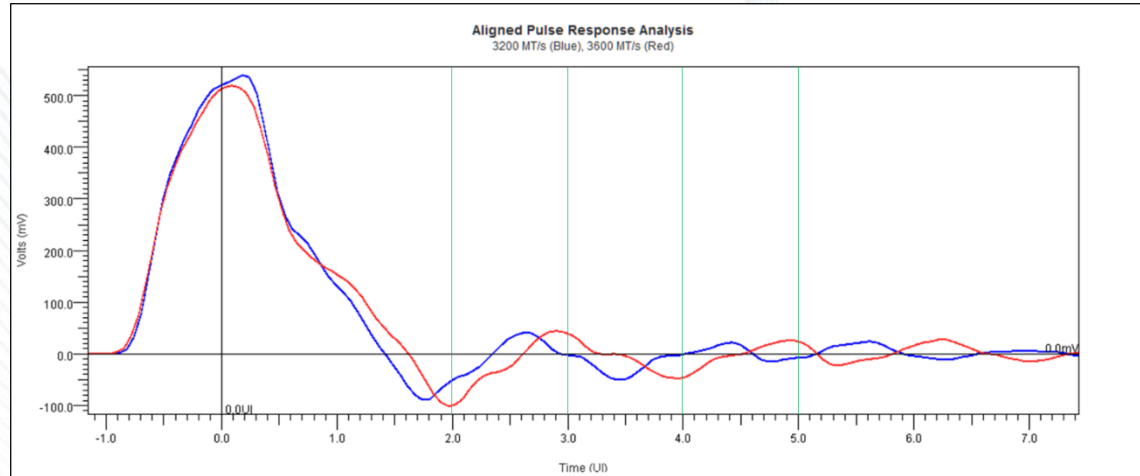
# Limiting Transaction vs. Speed



- Data rate: 3200 to 6400MT/s, increments of 400 MT/s
- Voltage margin against mask is plotted
- Two questions
  - Why is 3600 MT/s so much worse than 3200 MT/s?
  - How can 4400 MT/s be better than 3600 MT/s?

# Pulse Response Analysis

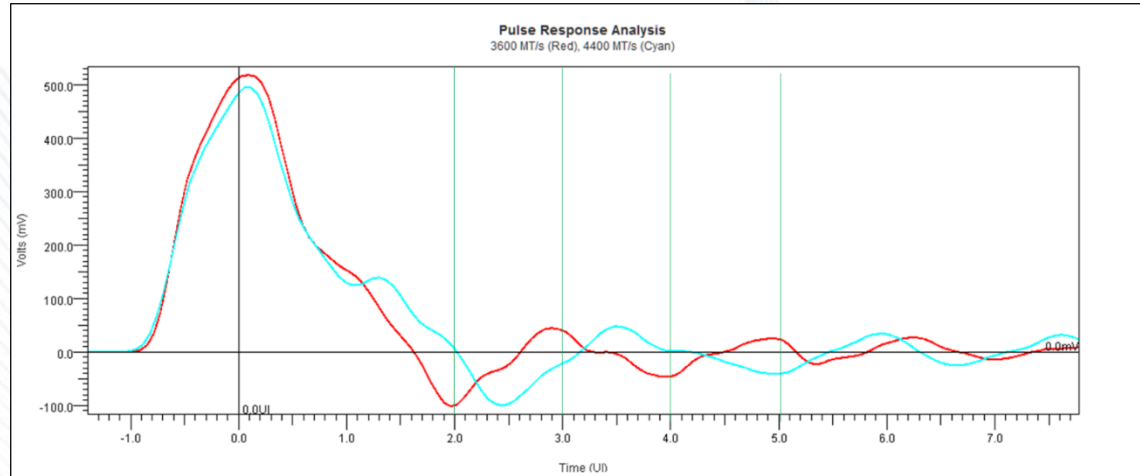
3200 MT/s (Blue) vs 3600 MT/s (Red)



- Vertical lines denote ISI at sampling times
- 3600 MT/s maximizes ISI at sample point

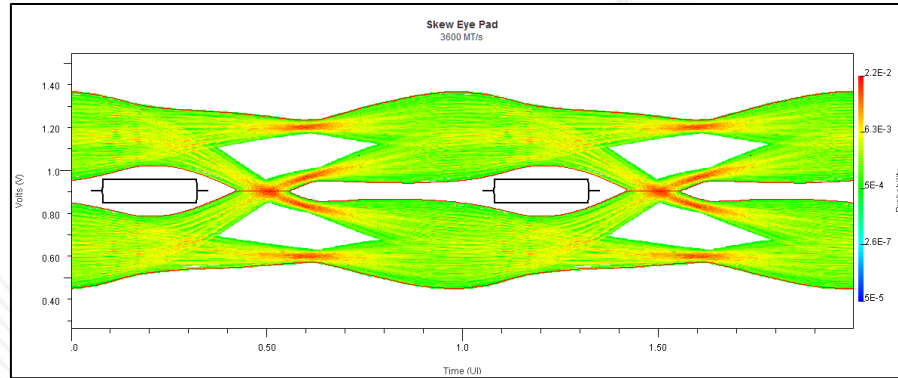
# Pulse Response Analysis

4400 MT/s (Cyan) vs 3600 MT/s (Red)

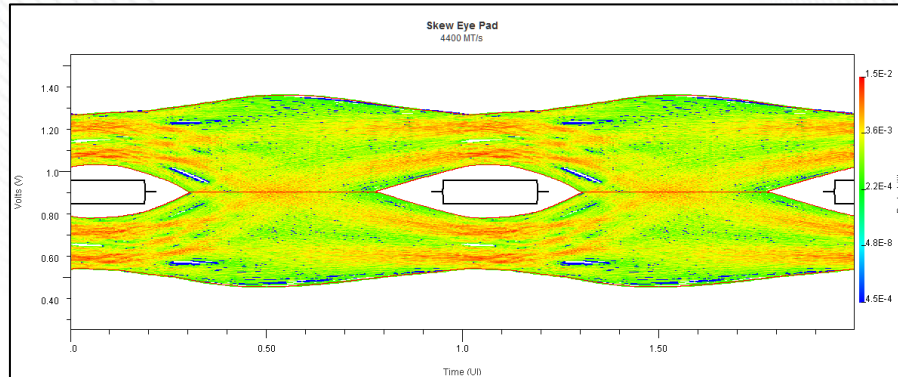


- 4400 MT/s has less pulse height & width
- 4400 MT/s ISI is much better than 3600 MT/s

# 3600 MT/s vs. 4400 MT/s

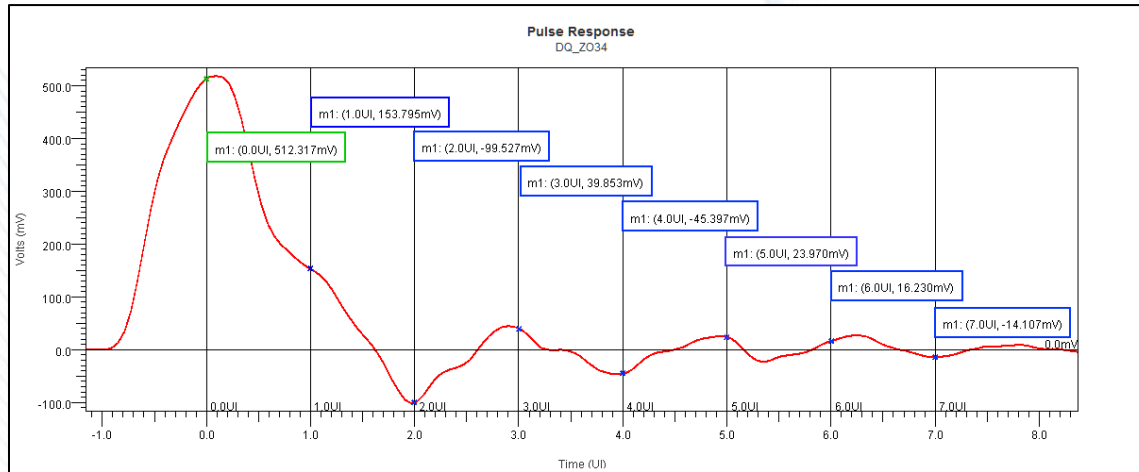


3600 MT/s



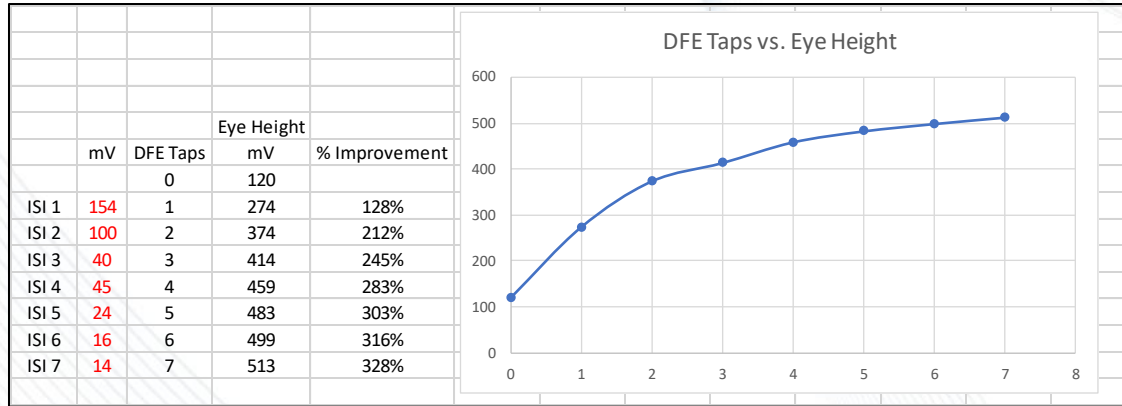
4400 MT/s

# Applying Equalization



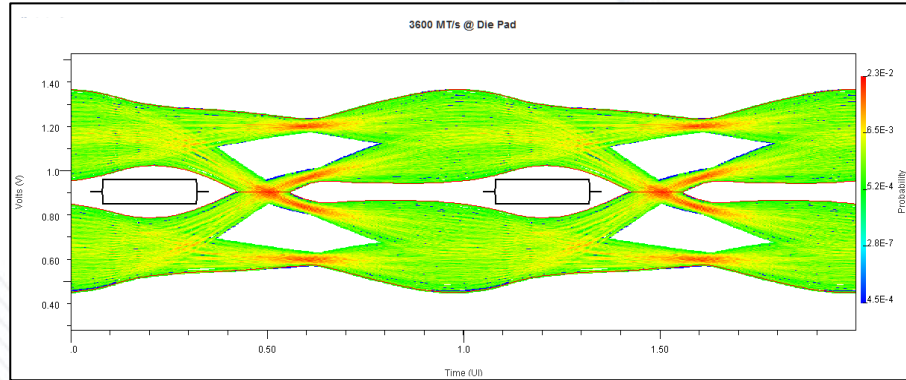
- Problem here isn't loss, it's ringing
- TX FIR and RX CTLE filters deal with loss
- RX DFE is best suited to correct ringing
- RX ISI voltages can be read directly off the plot

# Eye Height vs. DFE Taps

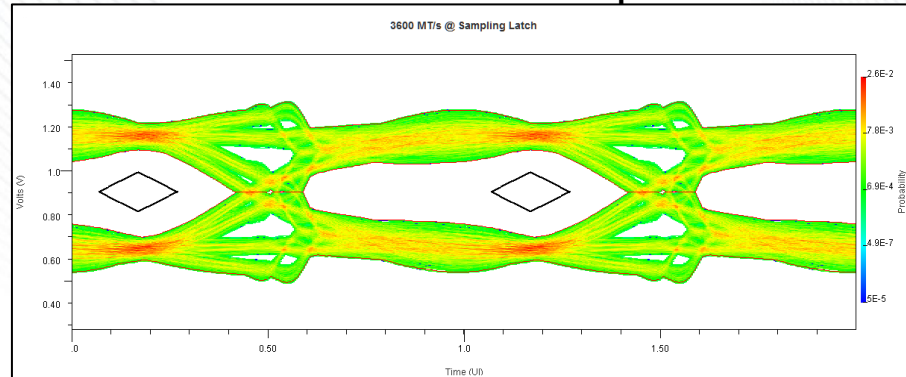


- We compute theoretical eye opening from the pulse response
- We also compute how DFE taps could improve eye height
  - Assumes tap range, granularity, training efficiency

# Impact of 2 DFE Taps



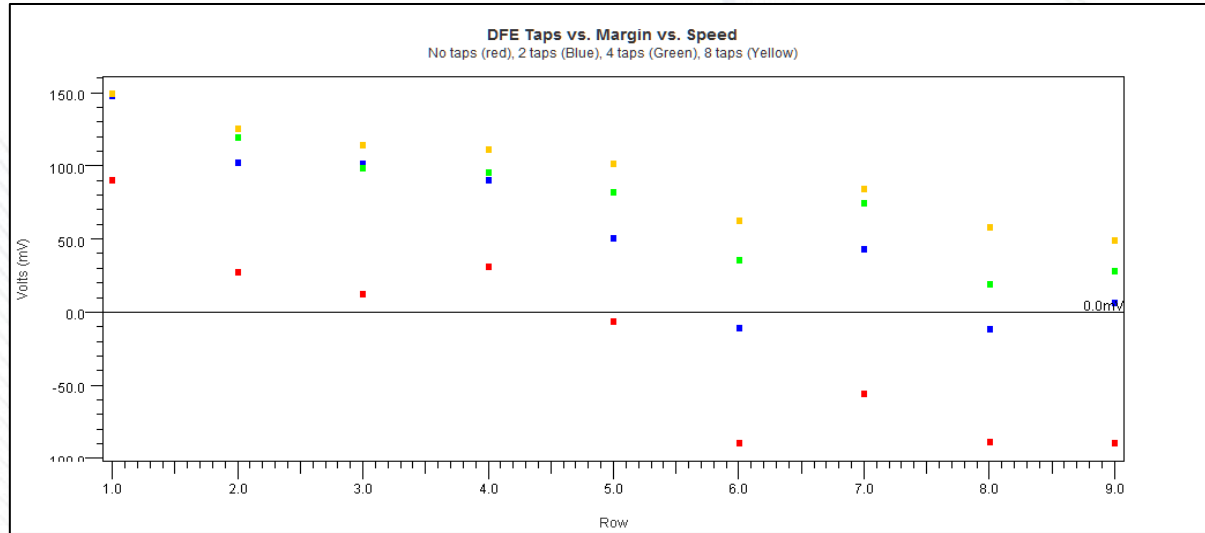
3600 MT/s @ die pad



3600 MT/s @ sampling latch

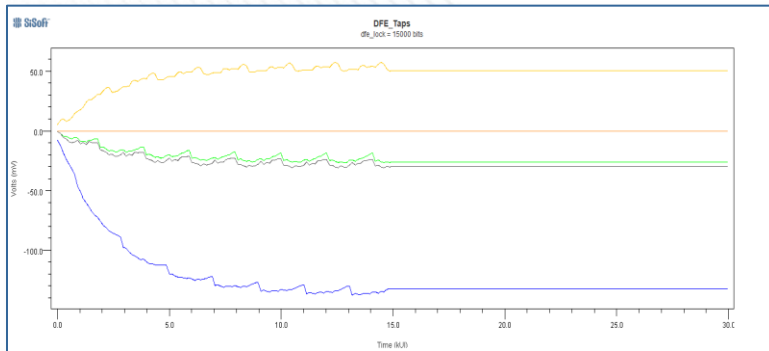
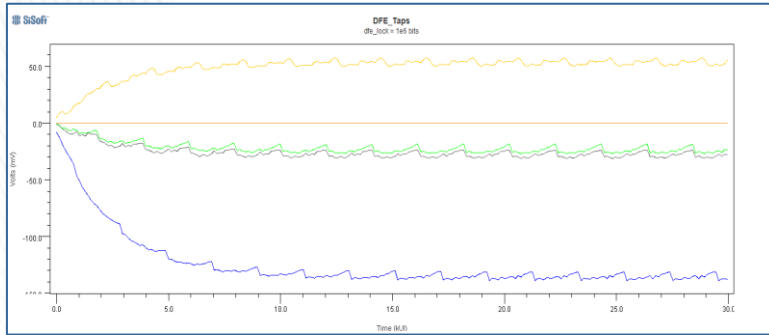


# DFE Taps vs. Speed



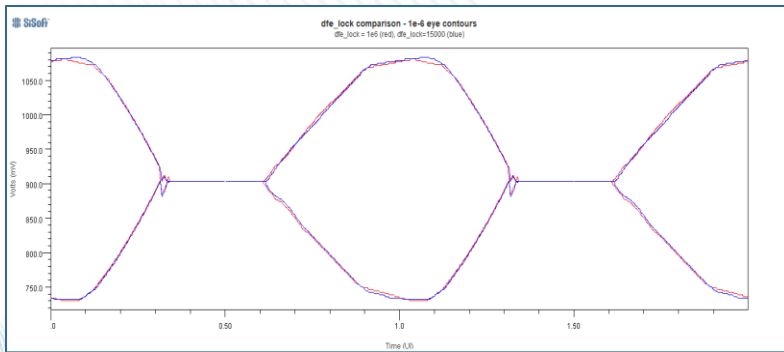
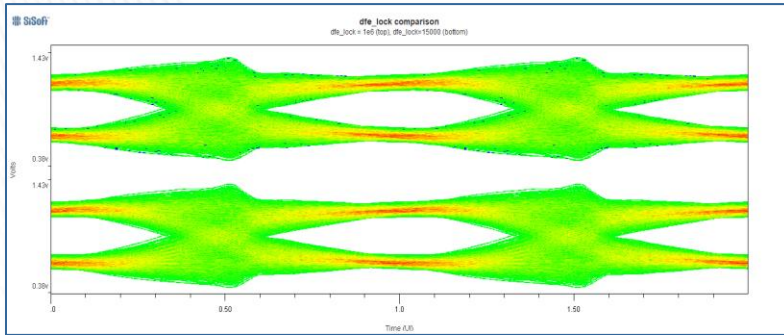
- Data rate: 3200 to 6400MT/s, increments of 400 MT/s
- Voltage margin against mask is plotted
- DFE taps: 0 (Red), 2 (Blue), 4 (Green), 8 (Yellow)

# Modeling DRAM DFE Training



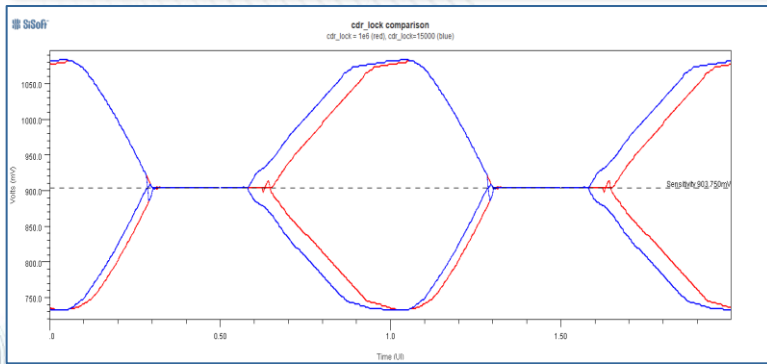
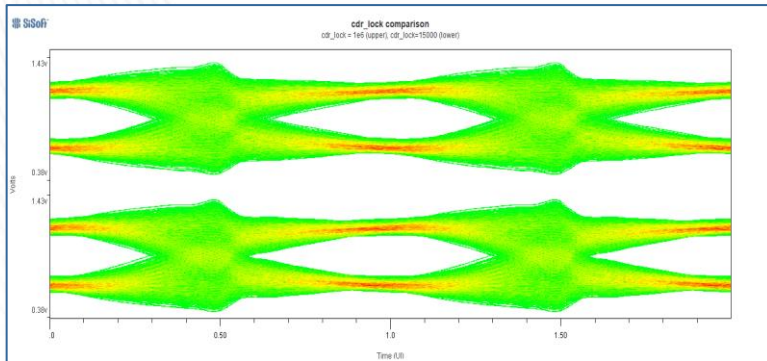
- DDR5 controllers set DRAM DFE taps by training at system startup
- Modeling training sequences with AMI models is difficult & time consuming
- Manually optimizing DRAM DFE settings through simulation is difficult & time consuming
- Approach: let DRAM DFE taps adapt, then lock settings when “Ignore\_Bits” is reached

# Modeling DRAM DFE Training



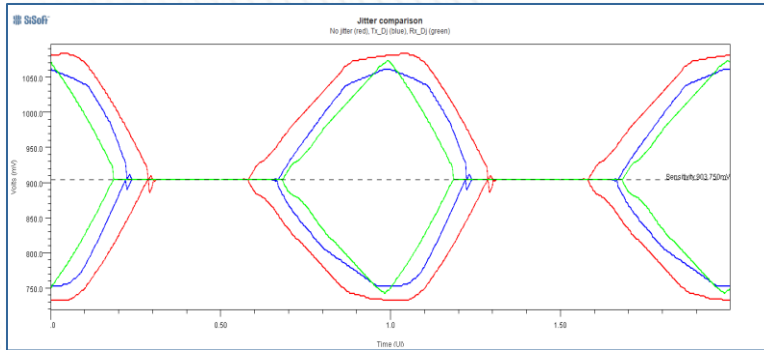
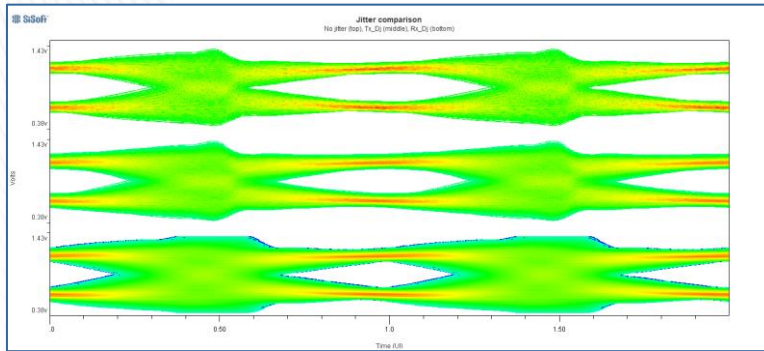
- How well does a “regular” adapting DFE model approximate an optimally trained, fixed-tap model?
  - Pretty well, in this example
  - Adapting (top eye, red contour)
  - Fixed (bottom eye, blue contour)
- In a pinch, an adapting DFE will probably give a reasonable estimate

# Modeling DQS Clock Forwarding



- DDR5 forwards the sampling clock via the DQS signal
- AMI models typically recover the clock from the incoming data
- “Locking the clock” in a typical AMI model approximates forwarded clock behavior
- Note that the “locked clock” contour (blue) is larger than its counterpart

# Modeling Tx and Rx Jitter



- Previous simulation results have omitted Tx/Rx jitter for simplicity
- AMI jitter / noise modeling
  - TX jitter directly modulates TX output
  - RX jitter modulates sampling clock
  - RX noise affects sampling latch input
- Effect RX eye contour
  - No jitter (red)
  - TX Dj (blue)
  - RX Dj (green)

# Summary

- Modern DDR analysis uses techniques that predict behavior over millions of data bits
- Optimizing driver / receiver termination settings is essential to ensuring margin
- Pulse response analysis provides useful insight into how ringing affects DDR design margins
- AMI models can be used to predict how Tx/Rx EQ will improve design margins
- This presentation only covered part of the full methodology needed for DDR5 analysis



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